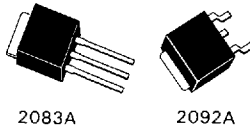


2SJ281



AP (Advanced Performance) Series
 $V_{DSS} = 250V$

P Channel Power MOSFET

©4243A

Features

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.

Absolute Maximum Ratings at $T_a = 25^\circ C$

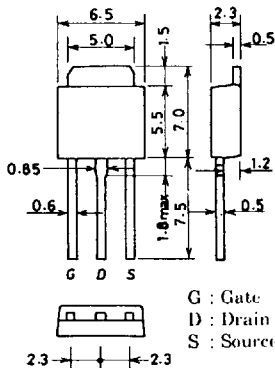
Parameter	Symbol	Value	unit
Drain to Source Voltage	V_{DSS}	-250	V
Gate to Source Voltage	V_{GSS}	± 30	V
Drain Current(DC)	I_D	-3	A
Drain Current(Pulse)	I_{DP}	-12	A
Allowable Power Dissipation	P_D	1.0	W
		$T_c = 25^\circ C$	
		30	W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

Electrical Characteristics at $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1mA, V_{GS} = 0$	-250			V
G-S Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 100\mu A, V_{DS} = 0$	± 30			V
Zero Gate Voltage	I_{DSS}	$V_{DS} = -250V, V_{GS} = 0$			-100	μA
Drain Current						
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 25V, V_{DS} = 0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10V, I_D = -1mA$	-1.5		-2.5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10V, I_D = -1.5A$	1.5	2.5		S
Static Drain to Source on State Resistance	$R_{DS(on)}$	$I_D = -1.5A, V_{GS} = -10V$		1.5	2.0	Ω
Input Capacitance	C_{iss}	$V_{DS} = -20V, f = 1MHz$		420		pF
Output Capacitance	C_{oss}	$V_{DS} = -20V, f = 1MHz$		100		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -20V, f = 1MHz$		40		pF

Continued on next page.

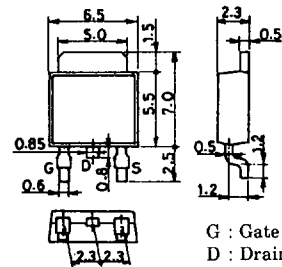
Package Dimensions 2083A
 (unit : mm)



G : Gate
 D : Drain
 S : Source

SANYO : TP

Package Dimensions 2092A
 (unit : mm)



G : Gate
 D : Drain
 S : Source

SANYO : TP-FA

Continued from preceding page.

			min	typ	max	unit
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		14		ns
Rise Time	t_r	"		18		ns
Turn-OFF Delay Time	$t_{d(off)}$	"		75		ns
Fall Time	t_f	"		65		ns
Diode Forward Voltage	V_{SD}	$I_S = -3A, V_{GS} = 0$	-1.0	-1.5		V

Switching Time Test Circuit

